MOBICON
Electronic Components

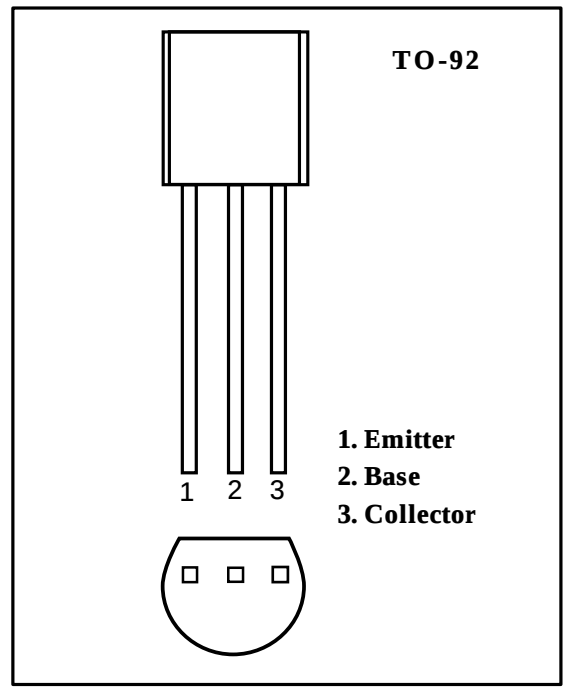
S@Tech KOREA

PNP EPITAXIAL SILICON TRANSISTOR

ST9018

High Frequency Low Noise Amplifier Application

- ◇ Collector Current Ic=-50mA
- ◇ Collector Power Dissipation Pc=625mW
- ◇ High Current Gain Bandwidth Product
  fT=1,100MHz (Typ)



ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	30	V
Collector-Emitter Voltage	V_{CEO}	15	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	50	mA
Collector Power Dissipation	P_C	400	mW
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55~ +150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C,unless otherwise specified)

Characteristic	Symbol	Test Condition	Min	TYP	MAX	Unit
Collector-base breakdown voltage	BV_{CBO}	I_C=100μA	30			V
Collector-emitter breakdown voltage	BV_{CEO}	I_C=1mA	15			V
Emitter-base breakdown voltage	BV_{EBO}	I_E=100μA	5			V
Collector cut-off current	I_{CBO}	V_{CB}=12V			50	nA
DC current gain	*hFE	I_C=1mA,V_{CE}=5V	54	100	198	
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=10mA,I_B=1mA			0.5	V
Output Capacitance	Cob	V_{CB}=10V,f=1MHz		1.3	1.7	pF
Transition Frequency	fT	V_{CE}=5V,I_C=5mA	700	1100		MHz

*** h_{FE} Classification: F: 54~80 , G: 72~108, H: 97~146, I: 132~198**

MADE IN KOREA

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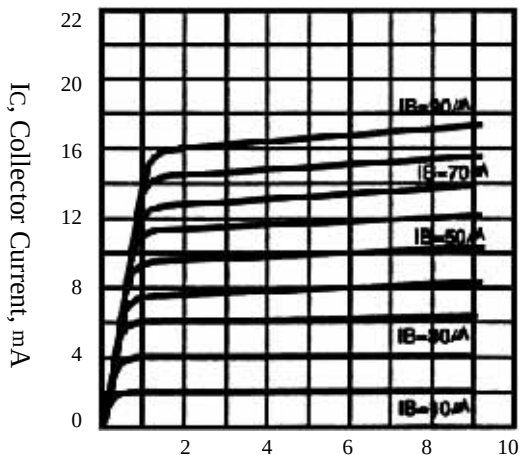
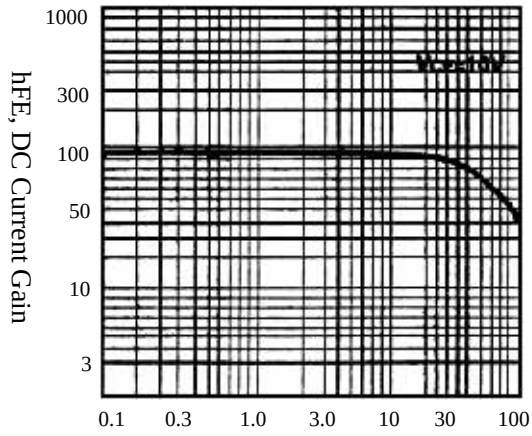
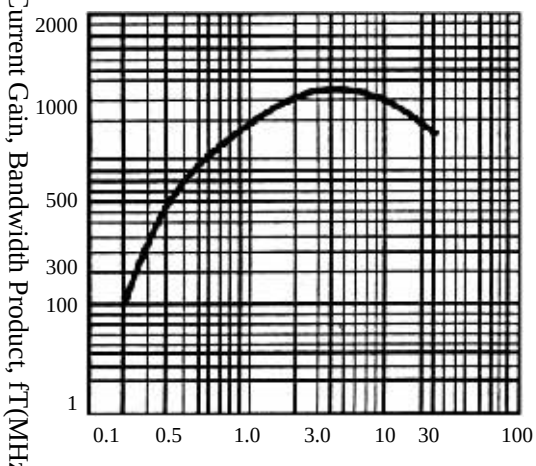
Static Characteristics



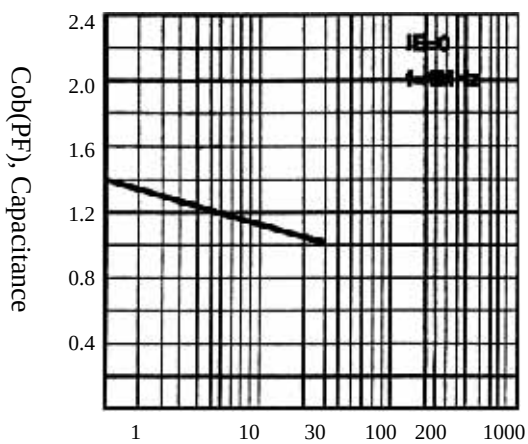
DC Current Gain



Current Gain-Bandwidth Product



Output Capacitance



Base Emitter Saturation Voltage
Collector Emitter Saturation Voltage